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(54) **Title:** SEMICONDUCTOR DEVICES WITH LOW PARASITIC CAPACITANCE

(57) **Abstract:** A semiconductor device with low parasitic capacitance comprises a substrate. The semiconductor device also comprises a gate region on the substrate. The semiconductor device further comprises a contact region on the substrate, wherein the contact region comprises a first portion and a second portion, wherein the first portion is in contact with the substrate and has a first surface above the substrate, and wherein the second portion is in contact with the substrate and has a second surface above the substrate different from the first surface.

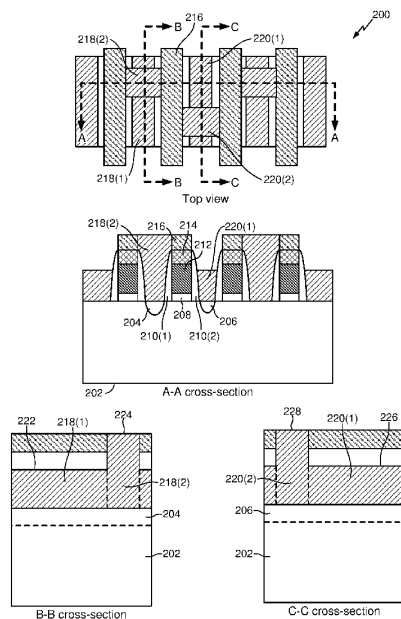


FIG. 2